

### **Amendments to the Claims:**

Please cancel Claims 1-9.

This listing of claims will replace all prior versions, and listings, of claims in the application.

### **Listing of Claims:**

Claims 1-9 (canceled)

Claim 10 (original): An electronic system formed in a semiconductor layer, comprising:  
a field effect transistor disposed in an active region of the outer surface of the semiconductor layer, the transistor comprising implanted regions proximate the periphery of the active region;

a field oxide layer on the outer surface of the semiconductor layer abutting the periphery of at least a portion of the active region; and

a channel stop implant region disposed in the semiconductor layer inwardly from portions of the field oxide layer and spaced apart from the periphery of the active region by an extension zone, the extension zone operable to inhibit the electrical interaction of the peripheral implanted regions of the transistor and the channel stop implant region.

Claim 11 (original): The electronic system of Claim 10 wherein the channel stop implant region comprises a first channel stop implant region and further comprising a second channel stop implant region disposed in the semiconductor layer inwardly from the field oxide layer and disposed at least partly in the extension zone.

Claim 12 (original): The electronic system of Claim 11 wherein the second channel stop implant region comprises implanted p-type impurities and the first channel stop implant comprises implanted n-type impurities.

Claim 13 (original): The electronic system of Claim 11 wherein the second channel stop implant region comprises implanted p-type impurities and the first channel stop implant comprises implanted n-type impurities.